

Microsemi.

Power Matters™

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Overview Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
DC Current Gain	HFE	30.00		120.00	
Turn Off Time (nS)	t _{off}			1250.00	ns

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector Current (dc)	I _C			25.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			100.00	V
Junction Temperature (°C)	T_J			200.00	°C

This part can be found in the following product categories:

- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor
- Discretes ► Transistors ► BJT(BiPolar Junction Transistor) ► PNP Transistor

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